



#5/PRE
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PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ohtani, et al. Art Unit: 2812
Serial No.: 09/379,702 Examiner:
Filed : August 24, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Assistant Commissioner for Patents
Washington, DC 20231

PRELIMINARY AMENDMENT

Sir:

Prior to initial examination, kindly amend the above-identified application as follows:

In the Claims:

Please cancel claim 1 without prejudice.

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OCT 07 1999

Please add the following new claims.

TECHNOLOGY CENTER 2800

2. A semiconductor device comprising:
a crystalline semiconductor layer comprising silicon over
a substrate; and

an insulating layer comprising a thermal oxide of said
semiconductor layer, said thermal oxide being provided in contact
with a surface of said semiconductor layer and constituting a part
of a gate insulating layer of said semiconductor device,

10/05/1999 ZABDALLA 00000044 09379702

01 FC:103
02 FC:102

414.00 OP
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Date of Deposit

9-27-99

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